

MASSACHUSETTS INSTITUTE OF TECHNOLOGY  
 Department of Electrical Engineering and Computer Science

6.012 ELECTRONIC DEVICES AND CIRCUITS

Problem Set No. 9

**Issued:** October 31, 2003

**Due:** November 12, 2003

**Reading Assignments:**

- Lecture 18 (11/4/03) - Chap. 11 (11.3 to end)
- Lecture 19 (11/6/03) - Chap. 12 (12.1, 12.2)
- Lecture 20 (11/13/03) - Chap. 12(12.3 to end); Chap. 13 (13.1)
- Lecture 21 (11/18/03) - Chap. 12 (12.4)
- Lecture 22 (11/20/03) - Chap. 14 (14.1, 14.2)
- Lecture 23 (11/25/03) - Chap. 13 (13.2 to end)

**Announcements:**

The **second hour exam** is scheduled for Wednesday night, November 5, from 7:30 to 9:30 pm in Room 10-250. The exam is closed book and will cover the material through 10/29/03 and Problem Set #8, including BJT operation and large signal modeling; the MOS capacitor; MOSFET operation and large signal modeling; incremental models for diodes, BJTs, and MOSFETs; and MOSFET inverters. There will be no weblab or HSPICE questions on the exam.

The **design problem** will be distributed on Friday, Nov. 7 and will be due on Wednesday, November 26. **Problem Set 9** (this one) is not due until Nov. 12, but you should try to finish it early so you can begin work on the design problem right away.

Problem 1 - Both parts of this problem deal with current mirrors for current source biasing:

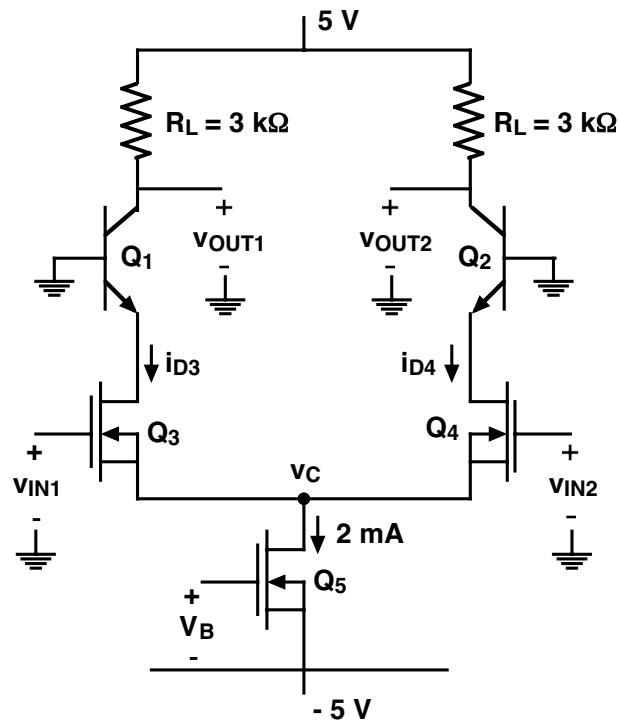
- a) Do Problem 11.1 in the course text.
- b) Do Problem 12.6 in the course text.

Problem 2 - Do Problem 11.6 in the course text.

Problem 3 - Do Problem 11.10 in the course text.

Problem 4 - The circuit on the next page uses three identical n-channel MOSFETs and two identical npn BJTs in a differential amplifier. Note that each side of the differential amplifier is a cascode circuit. The transistors have the following properties:

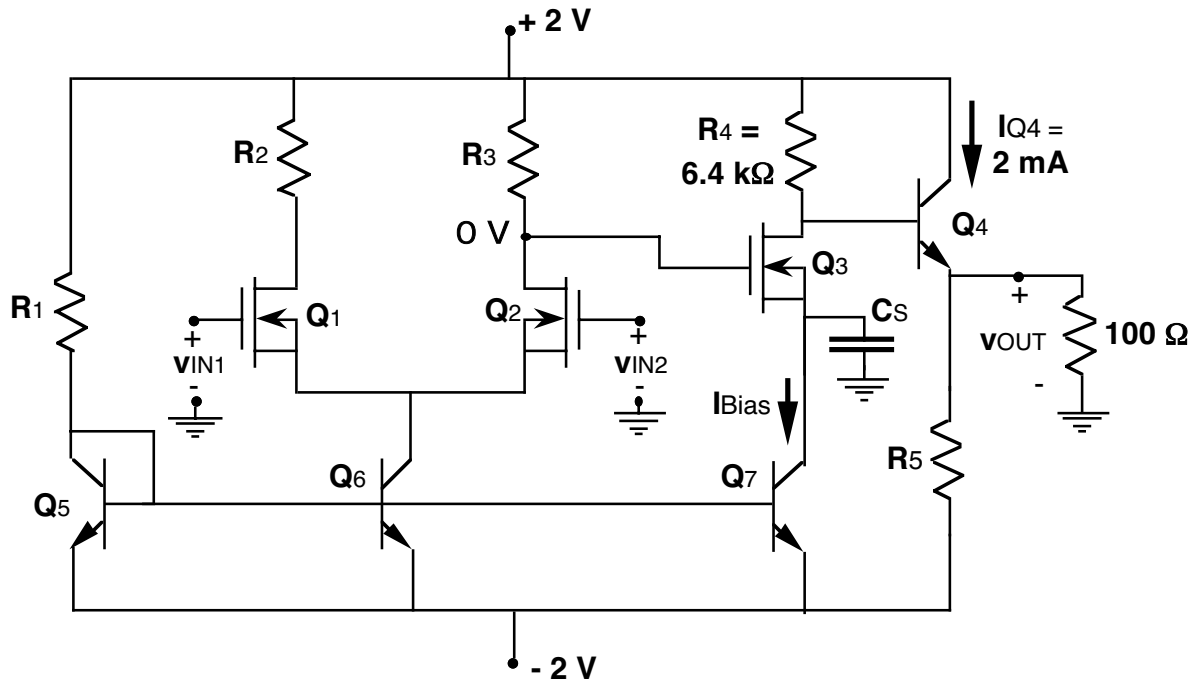
$$\begin{aligned} \text{n-channel MOSFETs: } & K = 2 \times 10^{-3} \text{ A/V}^2, V_T = 1 \text{ V}, |V_a| = 20 \text{ V} \\ \text{nnp BJTs: } & \beta = 100, v_{BE} \cong 0.6 \text{ V}, |V_a| = 100 \text{ V} \end{aligned}$$



- a) With both inputs zero (i.e.  $v_{IN1} = v_{IN2} = 0$ ) determine the indicated quiescent currents and voltages. Specify units:
- |                              |                                 |
|------------------------------|---------------------------------|
| i) $I_{D3}$ ( $= I_{D4}$ )   | ii) $V_{OUT1}$ ( $= V_{OUT2}$ ) |
| iii) $V_C$                   | iv) $V_{CE1}$ ( $= V_{CE2}$ )   |
| v) $V_{DS3}$ ( $= V_{DS4}$ ) |                                 |
- b) Draw two mid-band linear equivalent half circuits (LEHCs) for this differential amplifier, one for common-mode inputs and one for difference-mode inputs. Label all of the elements in your schematics.
- c) Derive literal expressions for the common-mode and difference-mode voltage gains,  $A_{vc}$  and  $A_{vd}$ , respectively, of this differential amplifier. The output conductances of  $Q_1$ ,  $Q_2$ ,  $Q_3$ , and  $Q_4$  are of insignificant effect and should be neglected in these derivations.

**Problem 5** - Consider the differential amplifier circuit illustrated on the next page. In this circuit the three n-channel MOSFETs are identical; they have a threshold voltage,  $V_T$ , of 1 V, a drain current in saturation of  $2.5(v_{GS} - V_T)^2$  mA, and an Early voltage of 10 V. The MOSFETs do not operate properly if  $(v_{GS} - V_T)$  is less than 0.2 V. The npn bipolar junction transistors (BJTs) all have forward betas,  $\beta_F$ , of 100, reverse betas,  $\beta_R$ , of 5, and an Early voltage of 50 V. The BJT sizes have been adjusted to that to a good approximation you may use  $|V_{BE,ON}| = 0.6$  V;  $|V_{CE,SAT}| = 0.2$  V. Assume  $C_S$  is a short at mid-band frequencies, and  $R_2$  and  $R_3$  are identical.

**Note:** The value of the resistor  $R_4$ , the quiescent collector current on  $Q_4$ , and minimum quiescent voltage on the gate of  $Q_3$  are indicated on the schematic, as are the supply voltages.



- a) What must the bias level ( $I_{Bias}$ ) on  $Q_3$  be to have a quiescent output voltage of approximately 0 V? (Assume that the quiescent collector current of  $Q_4$  is 2 mA, as indicated, and do not forget its base current.)
- b) Select  $R_5$  to be consistent with a quiescent collector current in  $Q_4$  of 2 mA, and a quiescent output voltage of approximately 0 V.
- c) Select  $R_1$  to give a bias current through  $Q_5$  of 1 mA. You may ignore the base currents of  $Q_5$ ,  $Q_6$ , and  $Q_7$ .
- d)
  - i) Draw a small signal linear equivalent half circuit one could use to calculate the signal voltage on the gate of  $Q_3$  due to the difference-mode input signal,  $v_{in1} - v_{in2}$ . Find an expression for this voltage in terms of incremental linear equivalent circuit model parameters.
  - ii) Write an expression for the differential-mode voltage gain of the differential stage ( $Q_1$ ,  $Q_2$ ) in terms of the resistors, the MOSFET  $K$ -factors, and the quiescent bias levels of  $Q_1$  and  $Q_2$ . Select  $R_2$  ( $= R_3$ ) and the drain current of  $Q_1$  and  $Q_2$  to maximize this voltage gain (magnitude).
- e) Suppose you can replace  $R_2$  and  $R_3$  with a current mirror made with p-channel MOSFETs with  $|V_T| = 1$  V and  $|V_A| = 20$  V. Draw the schematic of such a current mirror, and calculate what impact this would have on the voltage gain.
- f) Looking at the output stage, what are the most positive and negative values of  $v_{out}$  possible? Explain your answers.